Suppression of Leakage Current in SOI CMOS LSIs by Using Silicon-Sidewall Body-Contact (SSBC) Technology

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Abstract

This paper clarifies two SOI-specific leakage components, STI-induced punchthrough and gate-oxide leakage, found especially in large-scale integration, and proposes a new SOI technology: Silicon-Sidewall Body-Contact (SSBC). Without layout penalty and process complexity, SSBC realizes self-aligned body contact to the substrate, which suppresses gate-oxide leakage, and prevents the SOI body from being mechanically stressed, thus eliminating punchthrough leakage. SSBC is promising for scaled SOI CMOS LSIs.